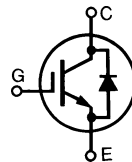


HiPerFAST™ IGBT with Diode

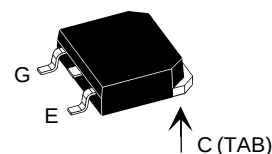
IXGH 30N60BD1
IXGT 30N60BD1

$$\begin{aligned} V_{CES} &= 600 \text{ V} \\ I_{C25} &= 60 \text{ A} \\ V_{CE(sat)} &= 1.8 \text{ V} \\ t_{fi(typ)} &= 100 \text{ ns} \end{aligned}$$

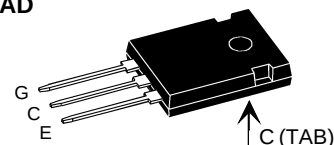


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	60	A
I_{C90}	$T_C = 90^\circ\text{C}$	30	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	120	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 10 \Omega$ Clamped inductive load, $L = 100 \mu\text{H}$	$I_{CM} = 60$ @ $0.8 V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	200	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum Lead and Tab temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque, TO-247 AD	1.13/10	Nm/lb.in.
Weight	TO-247 AD	6	g
	TO-268	4	g

TO-268
(IXGT)



TO-247 AD
(IXGH)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard package
- Moderate frequency IGBT and antiparallel FRED in one package
- High current handling capability
- Newest generation HDMOS™ process
- MOS Gate turn-on - drive simplicity

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages

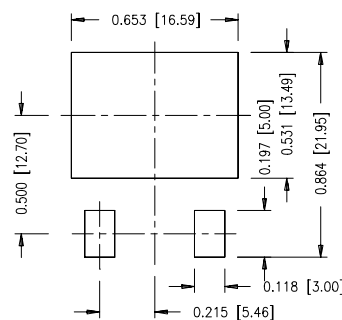
- Space savings (two devices in one package)
- High power density
- Optimized $V_{ce(sat)}$ and switching speeds for medium frequency application

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}$, $V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}$, $V_{CE} = V_{GE}$	2.5		5.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 150^\circ\text{C}$			200 μA 3 mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15 \text{ V}$			1.8 V

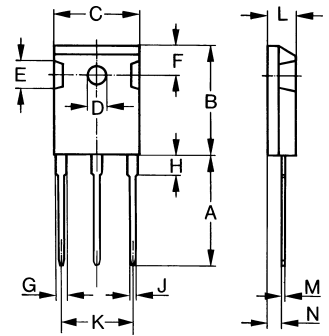
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}$; $V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$		25	S
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		2700	pF
C_{oes}			240	pF
C_{res}			50	pF
Q_g	$I_C = I_{C90}$; $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		110	nC
Q_{ge}			22	nC
Q_{gc}			40	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 4.7\text{ }\Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G		25	ns
t_{ri}			30	ns
$t_{d(off)}$			130	220 ns
t_{fi}			100	190 ns
E_{off}			1.0	2.0 mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 4.7\text{ }\Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G		25	ns
t_{ri}			35	ns
E_{on}			1.0	mJ
$t_{d(off)}$			200	ns
t_{fi}			230	ns
E_{off}			2.5	mJ
R_{thJC}	(TO-247 AD)			0.62 K/W
R_{thCK}			0.25	K/W

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_F	$I_F = I_{C90}$, $V_{GE} = 0\text{ V}$, Pulse test $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$	$T_J = 150^\circ\text{C}$		1.6 V 2.5 V
I_{RM}	$I_F = I_{C90}$, $V_{GE} = 0\text{ V}$, $-di_F/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$ $I_F = 1\text{ A}$; $-di/dt = 100\text{ A}/\mu\text{s}$; $V_R = 30\text{ V}$	$T_J = 100^\circ\text{C}$	6	A
t_{rr}			100	ns
t_{rr}			25	ns
R_{thJC}				0.9 K/W

Min. Recommended Footprint

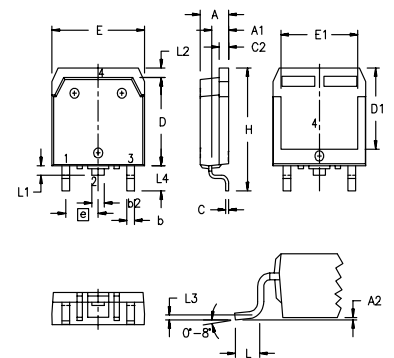


TO-247 AD (IXGH) Outline



Dim.	Millimeter Min. Max.	Inches Min. Max.
A	19.81 20.32	0.780 0.800
B	20.80 21.46	0.819 0.845
C	15.75 16.26	0.610 0.640
D	3.55 3.65	0.140 0.144
E	4.32 5.49	0.170 0.216
F	5.4 6.2	0.212 0.244
G	1.65 2.13	0.065 0.084
H	- 4.5	- 0.177
J	1.0 1.4	0.040 0.055
K	10.8 11.0	0.426 0.433
L	4.7 5.3	0.185 0.209
M	0.4 0.8	0.016 0.031
N	1.5 2.49	0.087 0.102

TO-268AA (D³ PAK)



Dim.	Millimeter Min. Max.	Inches Min. Max.
A	4.9 5.1	.193 .201
A ₁	2.7 2.9	.106 .114
A ₂	.02 .25	.001 .010
b	1.15 1.45	.045 .057
b ₂	1.9 2.1	.75 .83
C	.4 .65	.016 .026
D	13.80 14.00	.543 .551
E	15.85 16.05	.624 .632
E ₁	13.3 13.6	.524 .535
e	5.45 BSC	.215 BSC
H	18.70 19.10	.736 .752
L	2.40 2.70	.094 .106
L ₁	1.20 1.40	.047 .055
L ₂	1.00 1.15	.039 .045
L ₃	0.25 BSC	.010 BSC
L ₄	3.80 4.10	.150 .161

Fig. 1. Saturation Voltage Characteristics

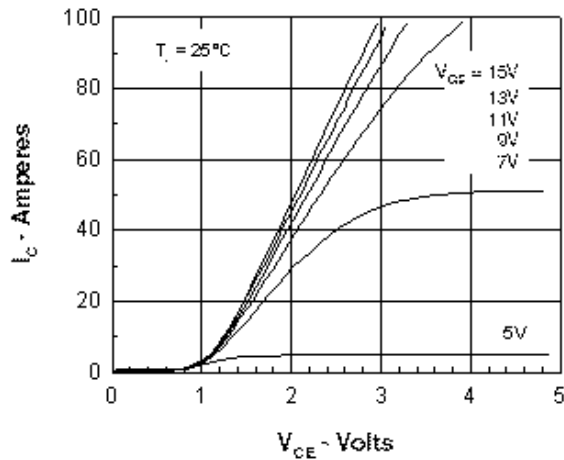


Fig. 2. Extended Output Characteristics

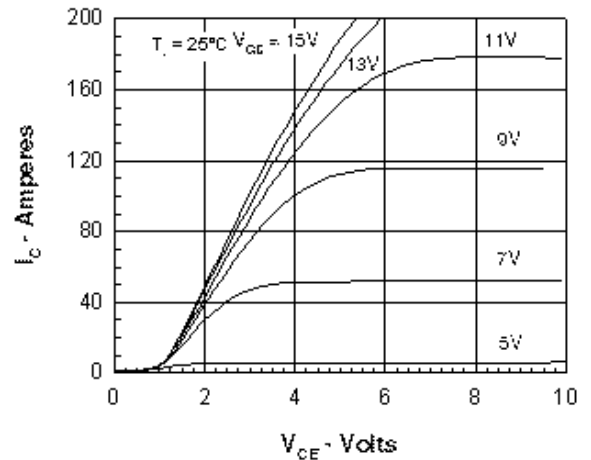


Fig. 3. Saturation Voltage Characteristics

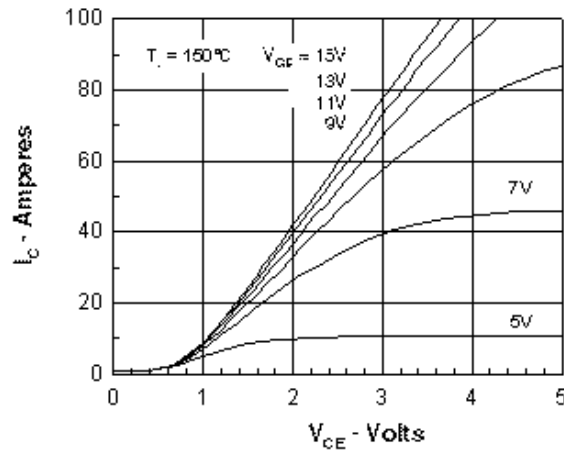
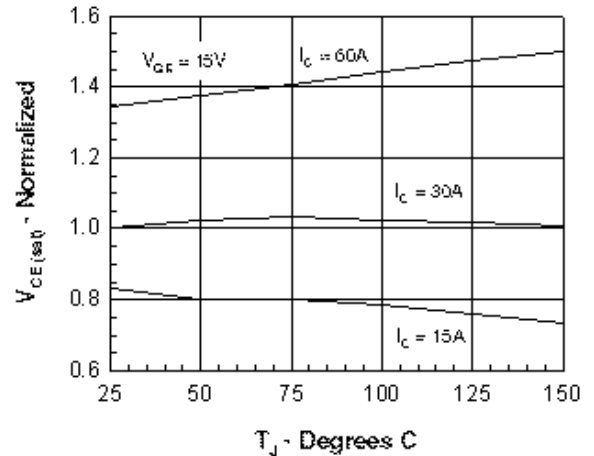

 Fig. 4. Temperature Dependence of $V_{CE(sat)}$


Fig. 5. Admittance Curves

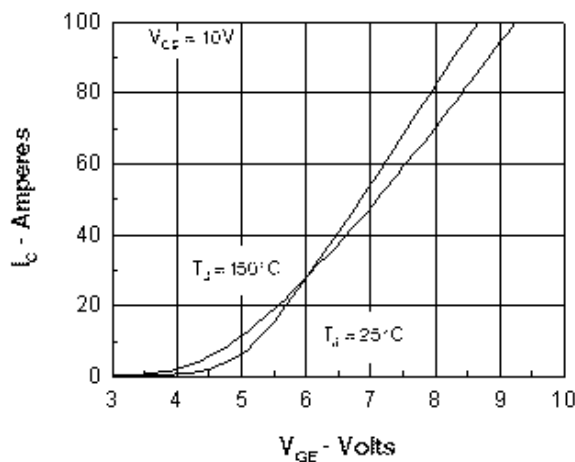
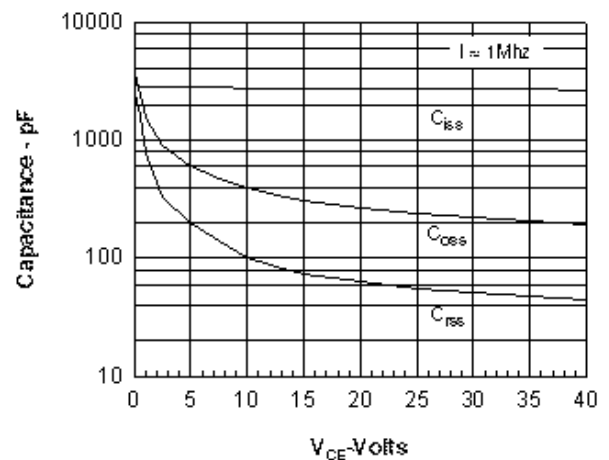

 Fig. 6. Temperature Dependence of BV_{DSS} & $V_{GE(th)}$


Fig. 7. Dependence of E_{OFF} and E_{ON} on I_C .

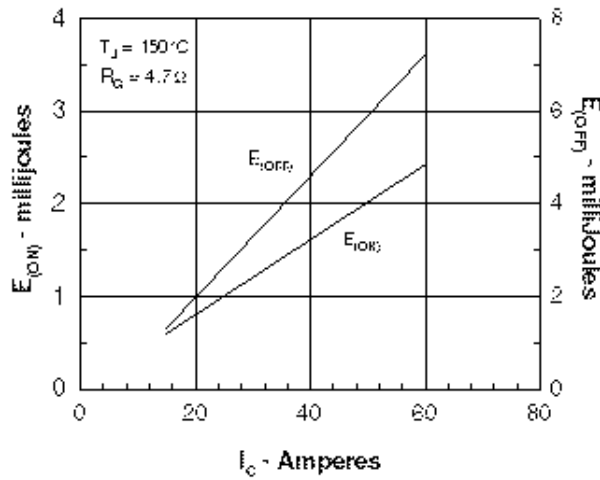


Fig. 8. Dependence of E_{OFF} on R_G .

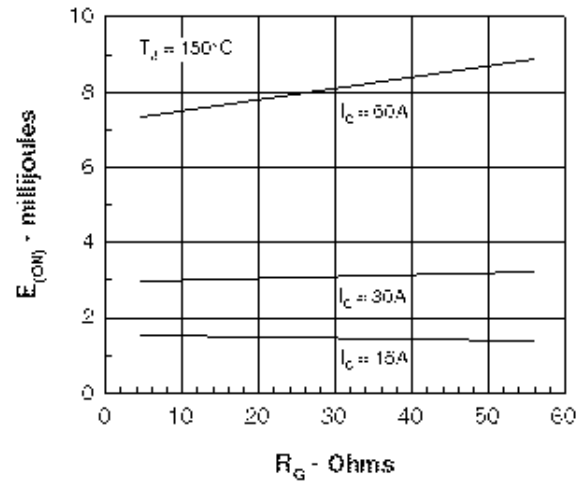


Fig. 9. Gate Charge

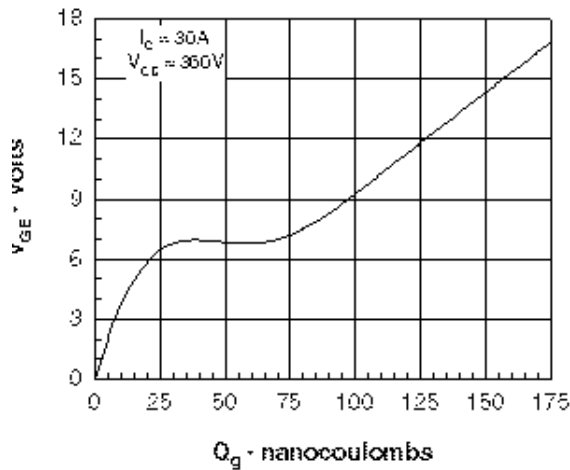


Fig. 10. Turn-off Safe Operating Area

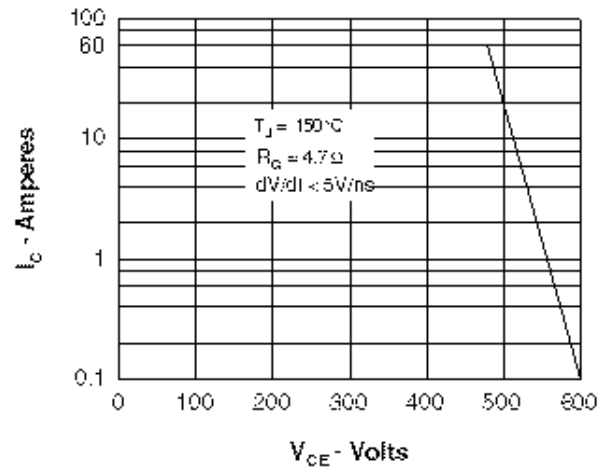
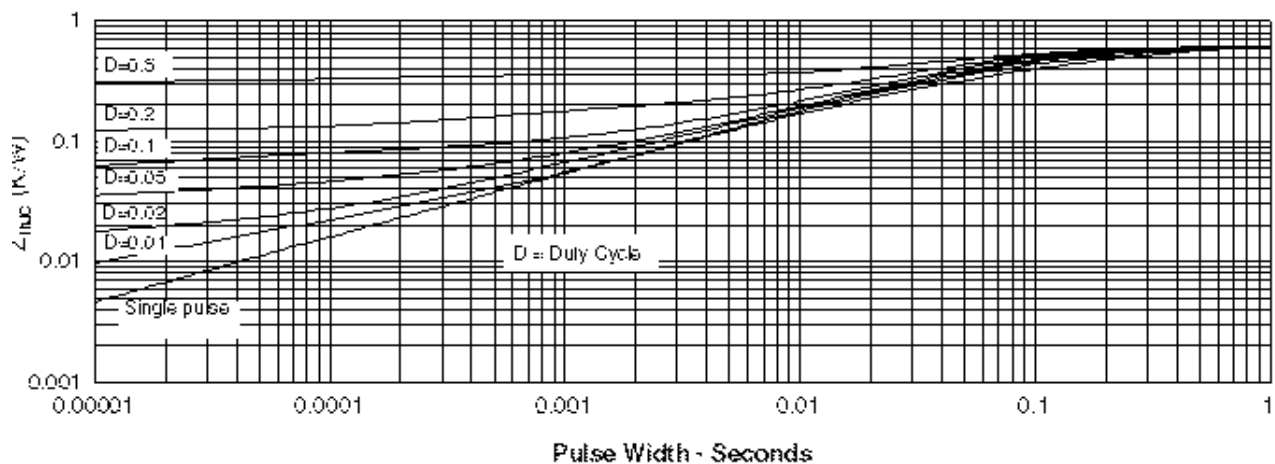


Fig. 11. IGBT Transient Thermal Resistance



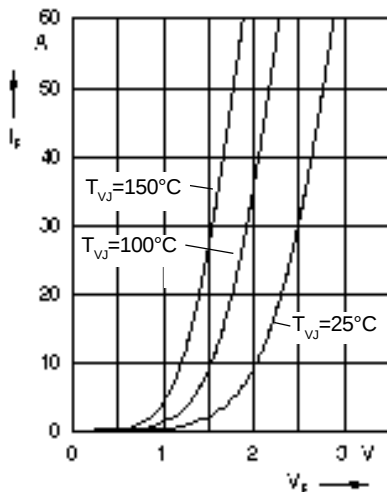


Fig. 12 Forward current I_F versus V_F

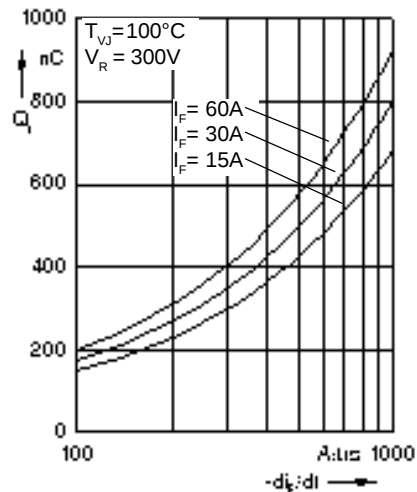


Fig. 13 Reverse recovery charge Q_r versus $-di_F/dt$

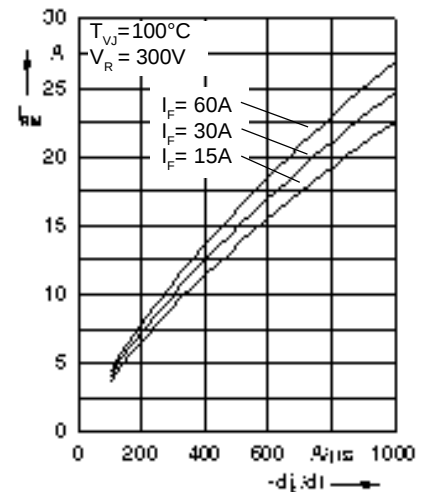


Fig. 14 Peak reverse current I_{RM} versus $-di_F/dt$

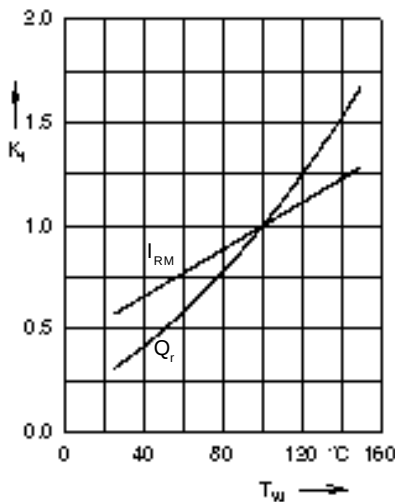


Fig. 15 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

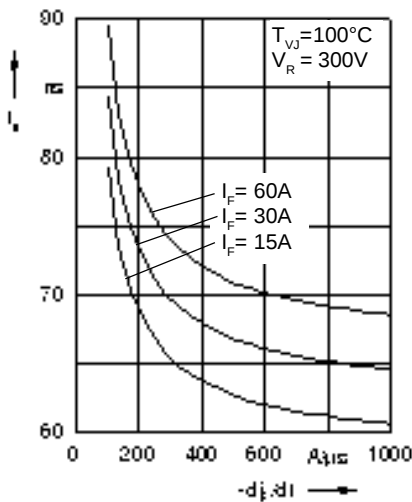


Fig. 16 Recovery time t_{tr} versus $-di_F/dt$

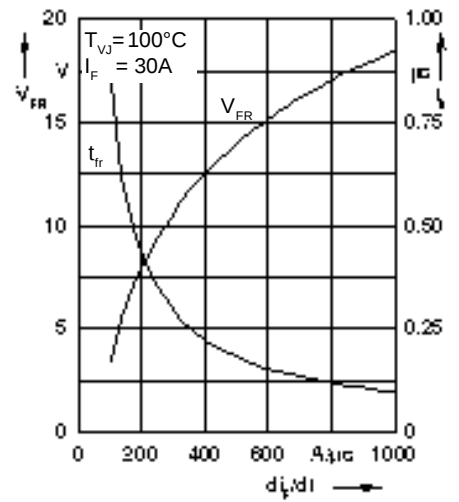


Fig. 17 Peak forward voltage V_{FR} and t_{tr} versus di_F/dt

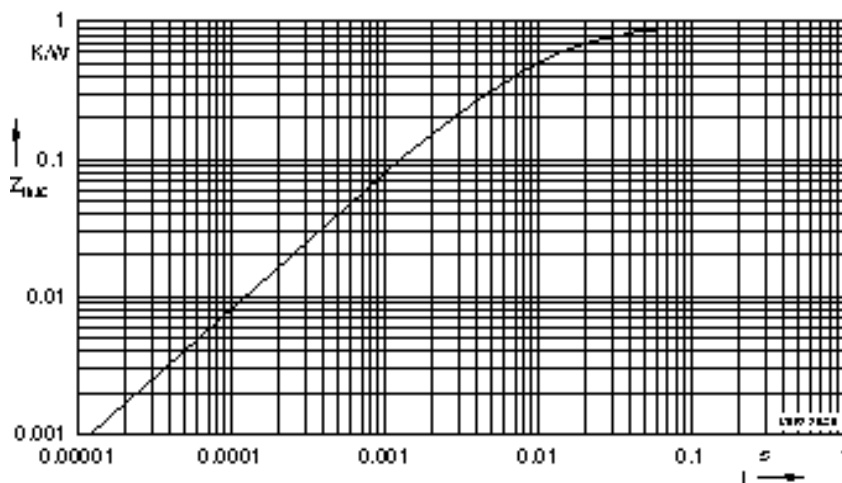


Fig. 18 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.502	0.0052
2	0.193	0.0003
3	0.205	0.0162